

ABSTRACT OF THE DISCLOSURE

There is provided a semiconductor device including a storage capacitor having sufficient capacity and a minimum area. The storage capacitor of a pixel region has such a structure that a first storage capacitor and a second storage capacitor are stacked one on top of the other and are connected in parallel with each other. At that time, the first storage capacitor comprises a first capacitance electrode formed in the same layer as a drain region, a first dielectric, and a second capacitance electrode formed in the same layer as a gate wiring. The second storage capacitor comprises the second capacitance electrode, a second dielectric, and a third capacitance electrode formed in the same layer as a light-shielding film.